

BC807H series

45 V, 500 mA PNP general-purpose transistors

Rev. 1 — 5 March 2019

Product data sheet

1. Product profile

1.1. General description

PNP general-purpose transistors in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package		Package		NPN comlement
	Nexperia	JEDEC			
BC807-16H	SOT23	TO-236AB	BC817K-16H		
BC807-25H			BC817K-25H		
BC807-40H			BC817K-40H		

1.2. Features and benefits

- · Three current gain selections
- High-temperature applications up to 175 °C
- AEC-Q101 qualified

1.3. Applications

· General-purpose switching and amplification

1.4. Quick reference data

Table 2. Quick reference data

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base		-	-	-45	V
I _C	collector current			-	-	-500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	-1	Α
h _{FE}	DC current gain	$V_{CE} = -1 \text{ V}; I_{C} = -100 \text{ mA}$					
	BC807-16H		[1]	100	-	250	
	BC807-25H		[1]	160	-	400	
	BC807-40H		[1]	250	-	600	

[1] pulsed; $t_p \le 300 \ \mu s$; $\delta \le 0.02$



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2. Pinning information

Table 3. Pinning

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base]3	C
2	Е	emitter		B—
3	С	collector		
				E sym132
			1	3,

3. Ordering information

Table 4. Ordering information

Type number	Package	Package						
	Name	Description	Version					
BC807-16H	TO-236AB	plastic, surface-mounted package; 3 leads	SOT23					
BC807-25H								
BC807-40H								

4. Marking

Table 5. Marking

Type number		Marking code
BC807-16H	[1]	65%
BC807-25H	[1]	6T%
BC807-40H	[1]	6U%

[1] % = placeholder for manufacturing site code

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5. Limiting values

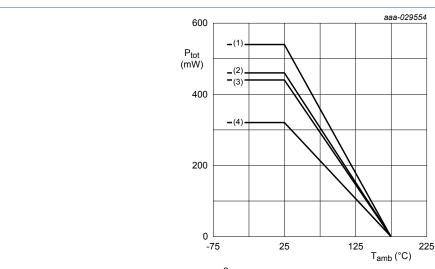
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter	open emitter		-50	V
V _{CEO}	collector-emitter voltage	open base		-	-45	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-1	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	-200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	320	mW
			[2]	-	440	mW
			[3]	-	460	mW
			[4]	-	540	mW
Tj	junction temperature			-	175	°C
T _{amb}	ambient temperature			-55	175	°C
T _{stg}	storage temperature			-65	175	°C

- [1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 1 cm².
- Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin plated and standard footprint.
- [4] Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated; mounting pad for collector 1 cm.²



- 1. FR4 PCB; 4-layer copper, 1cm²
- 2. FR4 PCB; 4-layer copper, standard footprint
- 3. FR4 PCB; single-sided copper, 1cm²
- 4. FR4 PCB; single-sided copper, standard footprint

Fig. 1. Power derating curves

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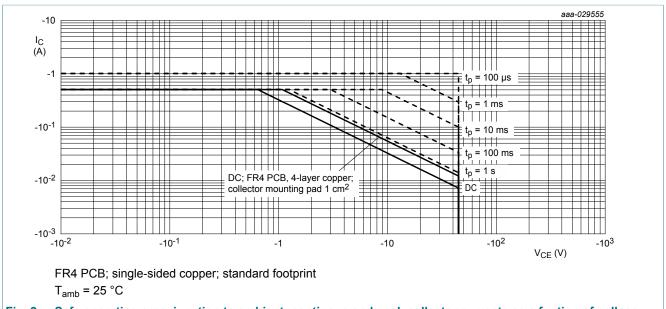


Fig. 2. Safe operating area; junction to ambient; continous and peak collector currents as a funtion of collecoremitter voltage

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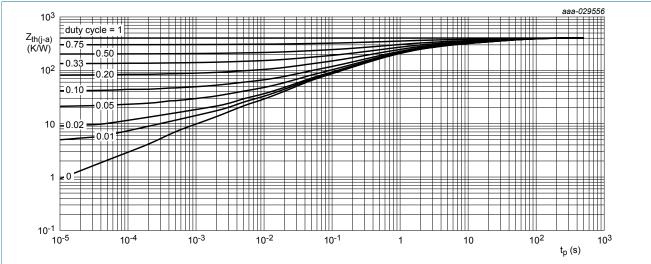
6. Thermal characteristics

Table 7. Thermal characteristics

 T_{amb} = 25 °C unless otherwise specified.

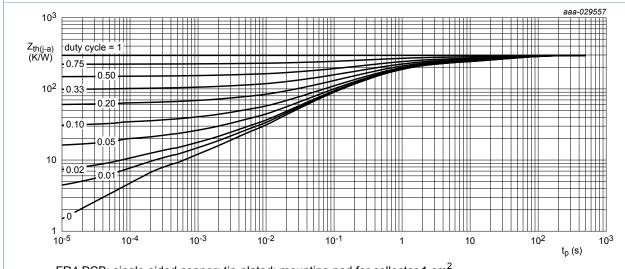
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	470	K/W
			[2]			340	K/W
			[3]			325	K/W
			[4]	-	-	280	K/W
R _(j-sp)	thermal resistance from junction to solder point			_	-	110	K/W

- [1] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated and standard footprint.
- [2] Device mounted on an FR4 Printed-Circuit-Board (PCB); single-sided copper; tin-plated; mounting pad for collector 1 cm².
- Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated and standard footprint.
- [4] Device mounted on an FR4 Printed-Circuit-Board (PCB); 4-layer copper; tin-plated; mounting pad for collector 1 cm².



FR4 PCB; single-sided copper; tin-plated and standard footprint

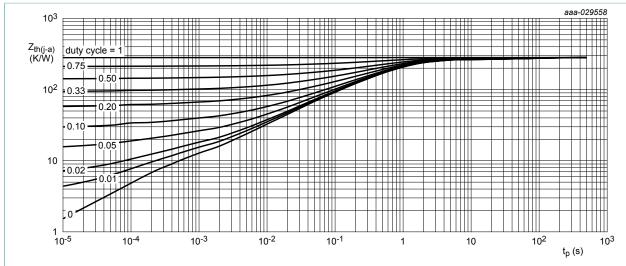
Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; single-sided copper; tin-plated; mounting pad for collector 1 cm²

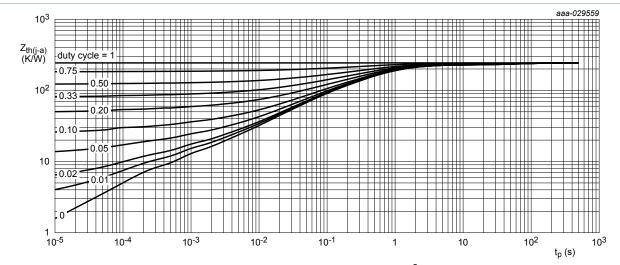
Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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FR4 PCB; 4-layer copper; tin-plated and standard footprint

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB; 4-layer copper; tin-plated; mounting pad for collector 1 cm²

Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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7. Characteristics

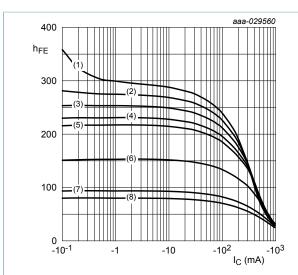
Table 8. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = -100 \ \mu A; I_E = 0 \ A$		-50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	_C = -10 mA; I _B = 0 A		-45	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage	$I_E = -100 \ \mu A; I_C = 0 \ A$		-7	-	-	V
I _{CBO}	collector-base	V _{CB} = -25 V; I _E = 0 A		-	-	-100	nA
	cut-off current	V _{CB} = -25 V; I _E = 0 A; T _j = 150 °C		-	-	-5	μA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain						
ВС	BC807-16H	V _{CE} = -1 V; I _C = -100 mA	[1]	100	-	250	
	BC807-25H		[1]	160	-	400	
	BC807-40H		[1]	250	-	600	
	DC current gain	V _{CE} = -1 V; I _C = -500 mA	[1]	40	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	[1]	-	-	-700	mV
V _{BEsat}	base-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	[1]			-1.2	V
V_{BE}	base-emitter voltage	$V_{CE} = -1 \text{ V; } I_{C} = -500 \text{ mA}$	[1]	-	-	-1.2	V
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz		80	-	-	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$		-	7	-	pF
Ce	emitter capacitance	$V_{EB} = -0.5 \text{ V}; I_C = I_C = 0 \text{ A}; f = 1 \text{ MHz}$					
	BC807-16H				50		pf
	BC807-25H				45		pF
	BC807-40H				37		pF

^[1] pulsed; $t_p \le 300 \ \mu s; \ \delta \le 0.02$

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 $V_{CE} = -1 V$

(1) $T_{amb} = 175 \, ^{\circ}C$

(2) $T_{amb} = 150 \, ^{\circ}C$

(3) T_{amb} = 125 °C

(4) $T_{amb} = 100 \, ^{\circ}C$

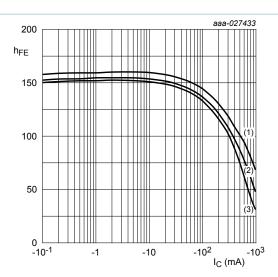
 $(5) T_{amb} = 85 °C$

(6) T_{amb} = 25 °C

(7) $T_{amb} = -40 \, ^{\circ}C$

(8) $T_{amb} = -55$ °C

Fig. 7. BC807-16H: DC current gain as a function of collector current; typical values



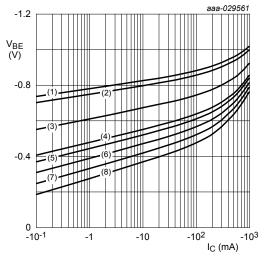
 $T_{amb} = 25 \, ^{\circ}C$

(1) $V_{CE} = -5 V$

(2) $V_{CE} = -2 V$

(3) $V_{CE} = -1 V$

Fig. 8. BC807-16H: DC current gain as a function of collector current; typical values



 $V_{CE} = -1 V$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = -40 \, ^{\circ}C$

(3) T_{amb} = 25 °C

(4) $T_{amb} = 85 \, ^{\circ}C$

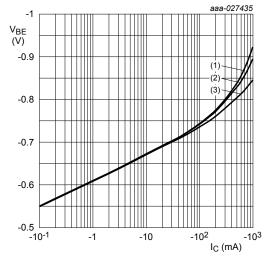
(5) $T_{amb} = 100 \, ^{\circ}C$

(6) $T_{amb} = 125 \, ^{\circ}C$

 $(7) T_{amb} = 150 °C$

(8) $T_{amb} = 175 \, ^{\circ}C$

Fig. 9. BC807-16H: Base-emitter voltage as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

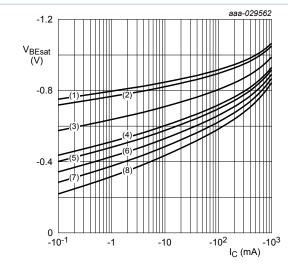
 $(1) V_{CE} = -1 V$

(2) $V_{CE} = -2 V$

(3) $V_{CE} = -5 V$

Fig. 10. BC807-16H: Base-emitter voltage as a function of collector current; typical values

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IC / IB = 10

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = -40 \, ^{\circ}C$

(3) T_{amb} = 25 °C

(4) T_{amb} = 85 °C

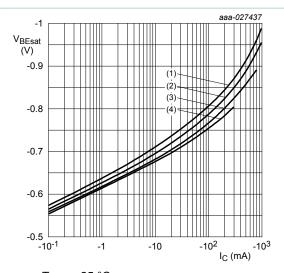
(5) $T_{amb} = 100 \, ^{\circ}C$

(6) $T_{amb} = 125 \, ^{\circ}C$

(7) $T_{amb} = 150 \, ^{\circ}C$

(8) T_{amb} = 175 °C

Fig. 11. BC807-16H: Base-emitter saturation voltage as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

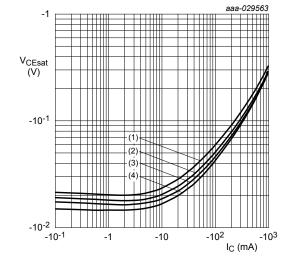
(1) IC / IB = 10

(2) IC / IB = 20

(3) IC / IB = 50

(4) IC / IB = 100

Fig. 12. BC807-16H: Base-emitter saturation voltage as a function of collector current; typical values



IC / IB = 10

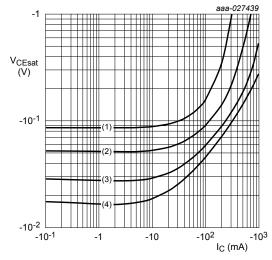
(1) $T_{amb} = 175 \, ^{\circ}C$

(2) T_{amb} = 85 °C

(3) $T_{amb} = 25 \, ^{\circ}C$

(4) $T_{amb} = -40 \, ^{\circ}C$

as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

(1) IC / IB = 100

(2) IC / IB = 50

(3) IC / IB = 20

(4) IC / IB = 10

Fig. 13. BC807-16H: Collector-emitter saturation voltage Fig. 14. BC807-16H: Collector-emitter saturation voltage as a function of collector current; typical values

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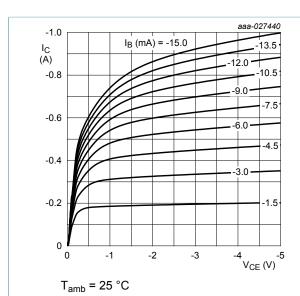
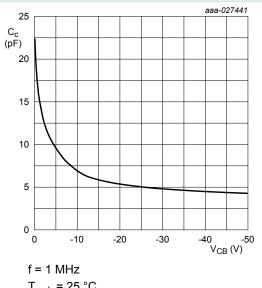


Fig. 15. BC807-16H: Collector current as a function of collector-emitter voltage; typical values



 T_{amb} = 25 °C

Fig. 16. BC807-16H: Collector capacitance as a function of collector-base voltage; typical values

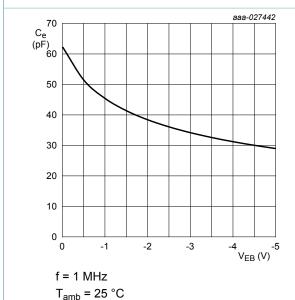
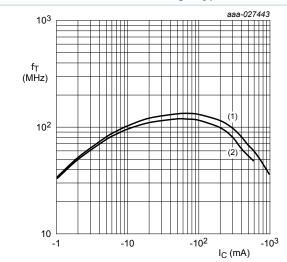


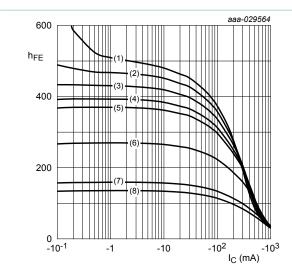
Fig. 17. BC807-16H: Emitter capacitance as a function of emitter-base voltage; typical values



f = 1 MHz T_{amb} = 25 °C (1) $V_{CE} = -5 V$ (2) $V_{CE} = -1 V$

Fig. 18. BC807-16H: Transition frequency as a function of collector current; typical values

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 $V_{CE} = -1 V$

(1) $T_{amb} = 175 \, ^{\circ}C$

(2) $T_{amb} = 150 \, ^{\circ}C$

(3) T_{amb} = 125 °C

(4) $T_{amb} = 100 \, ^{\circ}C$

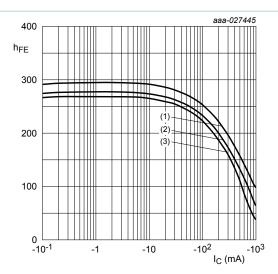
 $(5) T_{amb} = 85 °C$

(6) T_{amb} = 25 °C

 $(7) T_{amb} = -40 °C$

(8) $T_{amb} = -55$ °C

Fig. 19. BC807-25H: DC current gain as a function of collector current; typical values



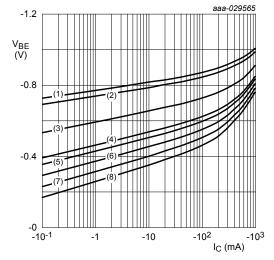
 T_{amb} = 25 °C

(1) $V_{CE} = -5 V$

(2) $V_{CE} = -2 V$

(3) $V_{CE} = -1 V$

Fig. 20. BC807-25H: DC current gain as a function of collector current; typical values



 $V_{CE} = -1 V$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = -40 \, ^{\circ}C$

(3) T_{amb} = 25 °C

(4) T_{amb} = 85 °C

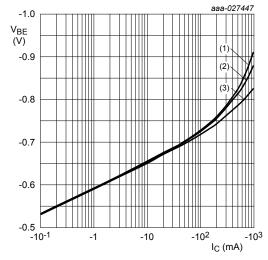
(5) $T_{amb} = 100 \, ^{\circ}C$

(6) $T_{amb} = 125 \, ^{\circ}C$

 $(7) T_{amb} = 150 °C$

(8) $T_{amb} = 175 \, ^{\circ}C$

Fig. 21. BC807-25H: Base-emitter voltage as a function of collector current; typical values



T_{amb} = 25 °C

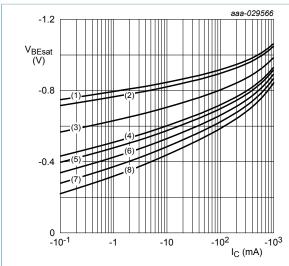
 $(1) V_{CE} = -1 V$

(2) $V_{CE} = -2 V$

(3) $V_{CE} = -5 V$

Fig. 22. BC807-25H: Base-emitter voltage as a function of collector current; typical values

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IC / IB = 10

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = -40 \, ^{\circ}C$

(3) T_{amb} = 25 °C

(4) T_{amb} = 85 °C

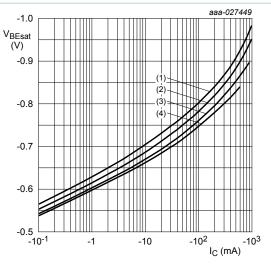
(5) $T_{amb} = 100 \, ^{\circ}C$

(6) $T_{amb} = 125 \, ^{\circ}C$

(7) $T_{amb} = 150 \, ^{\circ}C$

(8) T_{amb} = 175 °C

Fig. 23. BC807-25H: Base-emitter saturation voltage as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

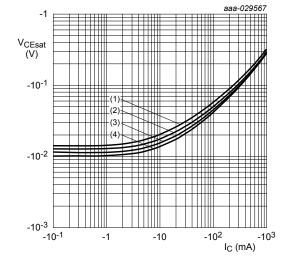
(1) IC / IB = 10

(2) IC / IB = 20

(3) IC / IB = 50

(4) IC / IB = 100

Fig. 24. BC807-25H: Base-emitter saturation voltage as a function of collector current; typical values



IC / IB = 10

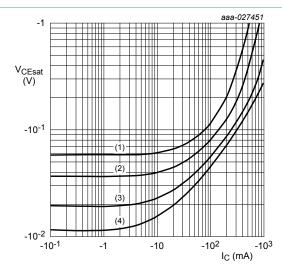
(1) $T_{amb} = 175 \, ^{\circ}C$

(2) T_{amb} = 85 °C

(3) $T_{amb} = 25 \, ^{\circ}C$

(4) $T_{amb} = -40 \, ^{\circ}C$

as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

(1) IC / IB = 100

(2) IC / IB = 50

(3) IC / IB = 20

(4) IC / IB = 10

Fig. 25. BC807-25H: Collector-emitter saturation voltage Fig. 26. BC807-25H: Collector-emitter saturation voltage as a function of collector current; typical values

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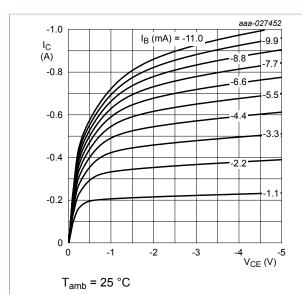
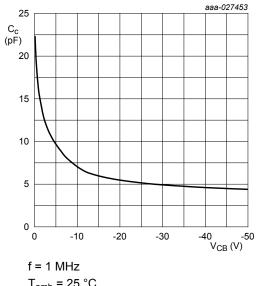


Fig. 27. BC807-25H: Collector current as a function of collector-emitter voltage; typical values



 T_{amb} = 25 °C

Fig. 28. BC807-25H: Collector capacitance as a function of collector-base voltage; typical values

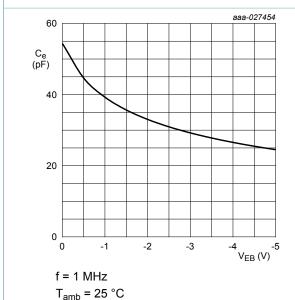
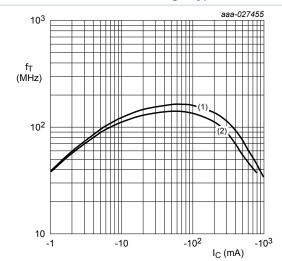


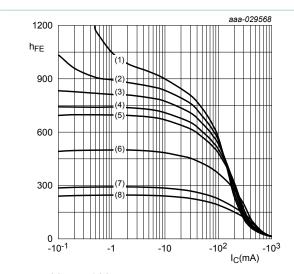
Fig. 29. BC807-25H: Emitter capacitance as a function of emitter-base voltage; typical values



f = 1 MHz T_{amb} = 25 °C (1) $V_{CE} = -5 V$ (2) $V_{CE} = -1 V$

Fig. 30. BC807-25H: Transition frequency as a function of collector current; typical values

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 $V_{CE} = -1 V$

(1) $T_{amb} = 175 \, ^{\circ}C$

(2) $T_{amb} = 150 \, ^{\circ}C$

(3) T_{amb} = 125 °C

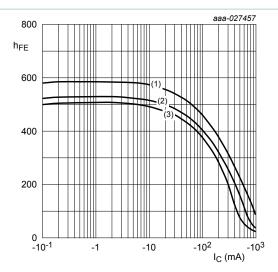
(4) T_{amb} = 100 °C

(5) T_{amb} = 85 °C

(6) $T_{amb} = 25 \, ^{\circ}C$ (7) $T_{amb} = -40 \, ^{\circ}C$

(8) $T_{amb} = -55 \, ^{\circ}C$

Fig. 31. BC807-40H: DC current gain as a function of collector current; typical values



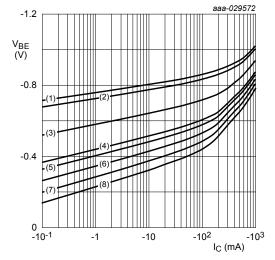
 T_{amb} = 25 °C

(1) $V_{CE} = -5 V$

(2) $V_{CE} = -2 V$

(3) $V_{CE} = -1 V$

Fig. 32. BC807-40H: DC current gain as a function of collector current; typical values



 $V_{CE} = -1 V$

(1) $T_{amb} = -55$ °C

(2) $T_{amb} = -40 \, ^{\circ}C$

(3) T_{amb} = 25 °C

(4) $T_{amb} = 85 \, ^{\circ}C$

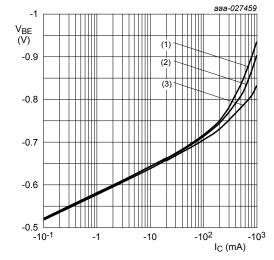
(5) $T_{amb} = 100 \, ^{\circ}C$

(6) $T_{amb} = 125 \, ^{\circ}C$

 $(7) T_{amb} = 150 °C$

(8) $T_{amb} = 175 \, ^{\circ}C$

Fig. 33. BC807-40H: Base-emitter voltage as a function of collector current; typical values



T_{amb} = 25 °C

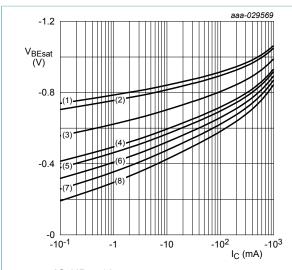
(1) $V_{CE} = -1 V$

(2) $V_{CE} = -2 V$

(3) $V_{CE} = -5 V$

Fig. 34. BC807-40H: Base-emitter voltage as a function of collector current; typical values

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IC / IB = 10

(1) $T_{amb} = -55 \, ^{\circ}C$

(2) $T_{amb} = -40 \, ^{\circ}C$

(3) T_{amb} = 25 °C

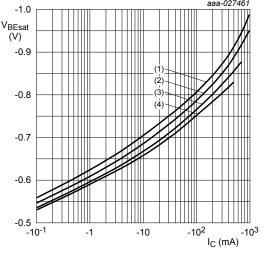
(4) T_{amb} = 85 °C

(5) $T_{amb} = 100 \, ^{\circ}C$

(6) $T_{amb} = 125 \, ^{\circ}C$

(7) $T_{amb} = 150 \, ^{\circ}C$

(8) T_{amb} = 175 °C



 $T_{amb} = 25 \, ^{\circ}C$

(1) IC / IB = 10

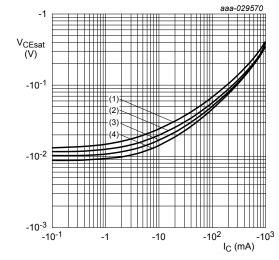
(2) IC / IB = 20

(3) IC / IB = 50

(4) IC / IB = 100

Fig. 36. BC807-40H: Base-emitter saturation voltage as a function of collector current; typical values





IC / IB = 10

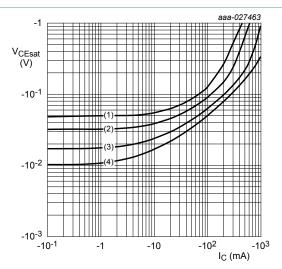
(1) $T_{amb} = 175 \, ^{\circ}C$

(2) T_{amb} = 85 °C

(3) T_{amb} = 25 °C

(4) $T_{amb} = -40 \, ^{\circ}C$

as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

(1) IC / IB = 100

(2) IC / IB = 50

(3) IC / IB = 20

(4) IC / IB = 10

Fig. 37. BC807-40H: Collector-emitter saturation voltage Fig. 38. BC807-40H: Collector-emitter saturation voltage as a function of collector current; typical values

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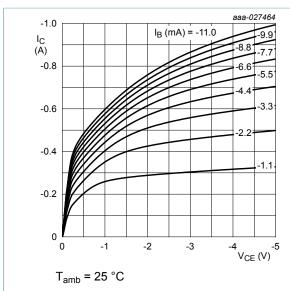


Fig. 39. BC807-40H: Collector current as a function of collector-emitter voltage; typical values

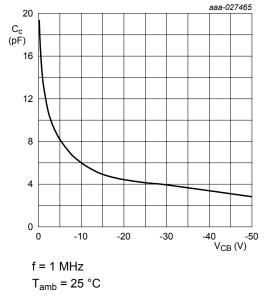


Fig. 40. BC807-40H: Collector capacitance as a function of collector-base voltage; typical values

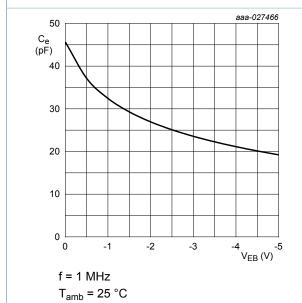
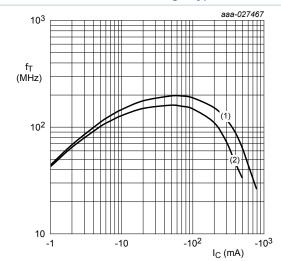


Fig. 41. BC807-40H: Emitter capacitance as a function of emitter-base voltage; typical values



f = 1 MHz $T_{amb} = 25 \text{ °C}$ $(1) V_{CE} = -5 V$ $(2) V_{CE} = -1 V$

Fig. 42. BC807-40H: Transition frequency as a function of collector current; typical values

8. Test information

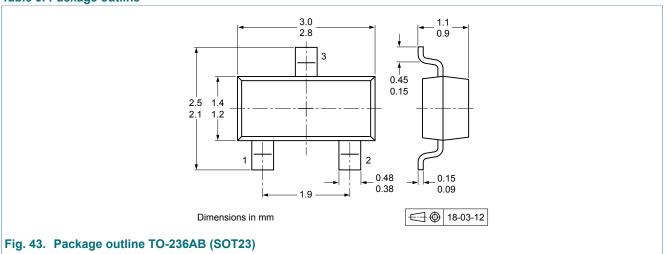
8.1. Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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9. Package outline

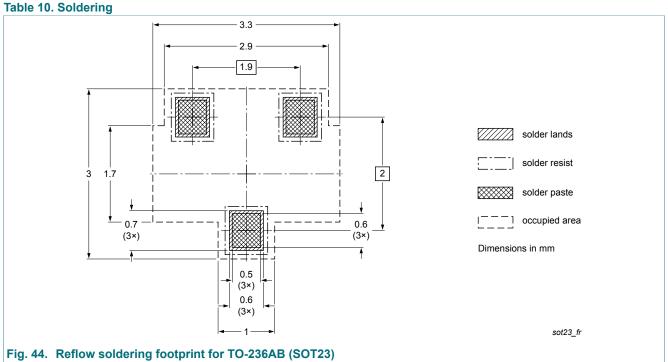
Table 9. Package outline

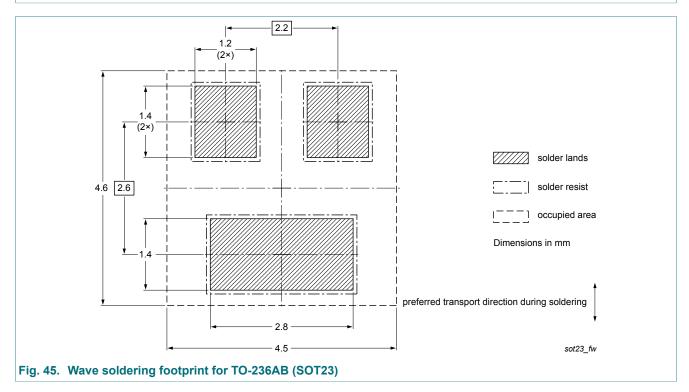


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10. Soldering







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11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC807H_SER v.1	20190305	Product data sheet	-	-

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- The term 'short data sheet' is explained in section "Definitions".
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For more information, please visit: http://www.nexperia.com For sales office addresses, please send an email to: salesaddresses@nexperia.com Date of release: 5 March 2019

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